

# **EXHIBIT 36C**

**PUBLIC VERSION – EXHIBIT REDACTED**

**REPRESENTATIVE CLAIM CHART ILLUSTRATING THE TECHNICAL PRONG OF DOMESTIC INDUSTRY  
FOR U.S. PATENT NO. 9,070,755 BASED ON INFINEON'S GS-065-011-1-L**

The following claim chart compares claim 1 of U.S. Patent No. 9,070,755 (“the ’755 Patent”) to Infineon’s GS-065-011-1-L 650 V E-mode GaN transistor (“GS-065-011-1-L”).

| '755 Patent Claim 1             | GS-065-011-1-L                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                 |
|---------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| [1PRE] A transistor comprising: | <p>To the extent the preamble is limiting, the preamble is met.</p> <p>Infineon’s GS-065-011-1-L, as shown below, is a transistor. For example, according to its datasheet, GS-065-011-1-L is an “enhancement mode GaN-on-Silicon power transistor.”</p> <p align="center">Description</p> <p align="center"><u>The GS-065-011-1-L is an enhancement mode GaN-on-Silicon power transistor. The properties of GaN allow for high current, high voltage breakdown and high switching frequency. GaN Systems innovates with industry leading advancements such as patented <b>Island Technology</b>® cell layout which realizes high-current die and high yield. The GS-065-011-1-L is a bottom-side cooled transistor that offers very low junction-to-case thermal resistance for demanding high power applications. These features combine to provide very high efficiency power switching.</u></p> <p align="center"><i>See Ex. 42 at 1 (GS-065-011-1-L Datasheet, annotations added)</i></p> |

| '755 Patent Claim 1                                                        | GS-065-011-1-L                                                                                                                                                                                                                                                                          |
|----------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                                                                            |                                                                                                                                                                                                       |
| [1A] drain finger electrodes interdigitated with source finger electrodes; | <p>Infineon's GS-065-011-1-L meets this limitation.</p> <p>As shown in [REDACTED] below, GS-065-011-1-L includes drain finger electrodes interdigitated with source finger electrodes. The drain finger electrodes and source finger electrodes are also illustrated in [REDACTED].</p> |



| '755 Patent Claim 1 | GS-065-011-1-L                                                                                                                                                                           |
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[Redacted]

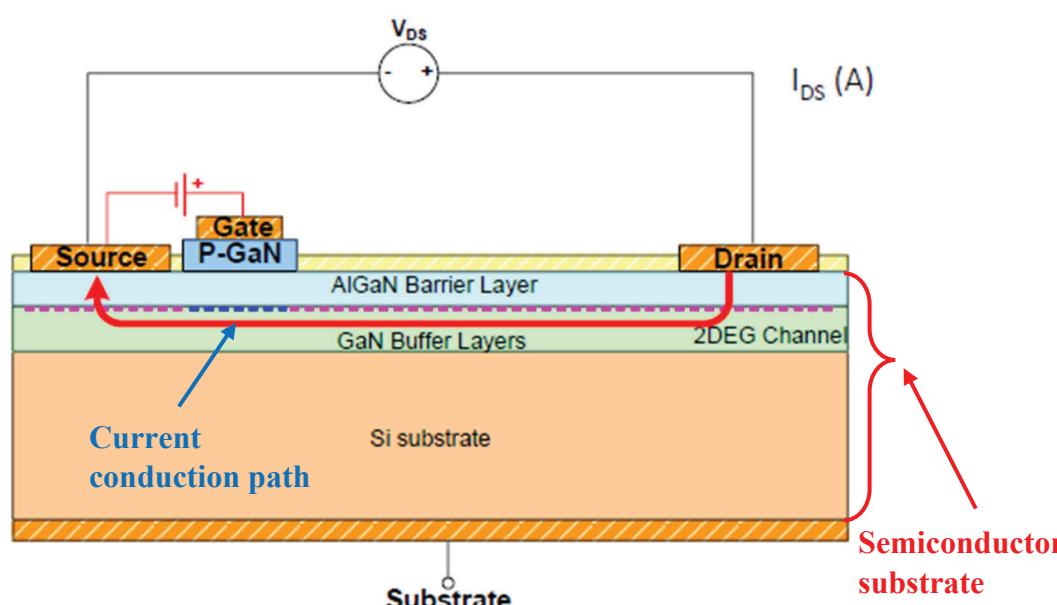
| '755 Patent Claim 1 | GS-065-011-1-L                                                                      |
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| '755 Patent Claim 1                                                                                                                | GS-065-011-1-L                                                                                                                                                                                                                  |
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|                                                                                                                                    |                                                                                                                                               |
| [1B] current conduction paths in a semiconductor substrate between said drain finger electrodes and said source finger electrodes; | <p>Infineon's GS-065-011-1-L meets this limitation.</p> <p>According to its datasheet, GS-065-011-1-L is an "enhancement mode GaN-on-Silicon power transistor," which comprises a semiconductor substrate (GaN-on-Silicon).</p> |



| '755 Patent Claim 1 | GS-065-011-1-L                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                       |
|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                     | <div><div>Applications</div><ul style="list-style-type: none"><li>• Power Adapters</li><li>• LED Lighting Drivers</li><li>• Fast Battery Charging</li><li>• Power Factor Correction</li><li>• Appliance Motor Drives</li><li>• Wireless Power Transfer</li><li>• Industrial Power Supplies</li></ul></div> <div><div>Description</div><p>The GS-065-011-1-L is an enhancement mode GaN-on-Silicon power transistor. The properties of GaN allow for high current, high voltage breakdown and high switching frequency. GaN Systems innovates with industry leading advancements such as patented <b>Island Technology</b>® cell layout which realizes high-current die and high yield. The GS-065-011-1-L is a bottom-side cooled transistor that offers very low junction-to-case thermal resistance for demanding high power applications. These features combine to provide very high efficiency power switching.</p></div> <div><p>See Ex. 42 at 1 (GS-065-011-1-L Datasheet)</p></div> <div><p>GS-065-011-1-L includes current conduction paths in a semiconductor substrate between said drain finger electrodes and said source finger electrodes, as shown in .</p></div> |

| '755 Patent Claim 1 | GS-065-011-1-L                                                                      |
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|                     |  |

| '755 Patent Claim 1                                                                                                                                                                                                                                  | GS-065-011-1-L                                                                                                                                                                                                                                                                                                                                                                                      |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                                                                                                                                                                                                                                                      | <p>As an additional example, the following Infineon document further illustrates current conduction paths in the semiconductor substrate between said drain finger electrodes and said source finger electrodes.</p>  <p>See Ex. 43 at 3 (“An Introduction to GaN Enhancement mode HEMTs”, annotations added)</p> |
| <p>[1C] at least one of said drain finger electrodes having a drain finger electrode main body and a drain finger electrode end, wherein at least a portion of said drain finger end is non-coplanar with said drain finger electrode main body.</p> | <p>Infineon’s GS-065-011-1-L meets this limitation.</p> <p><div></div> shows at least one of said drain finger electrodes having a drain finger electrode main body and a drain finger electrode end, wherein at least a portion of said drain finger end is non-coplanar with said drain finger electrode main body.</p>                                                                           |



| '755 Patent Claim 1 | GS-065-011-1-L                                                                                                                                                                                   |
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| '755 Patent Claim 1 | GS-065-011-1-L                                                                                                                                                                                                    |
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